

RB521CS-30

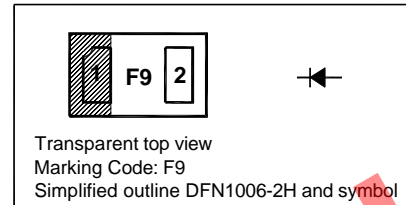
Silicon Epitaxial Planar Schottky Barrier Diode

Features

- Ultra small power mold type
- Low V_F
- High reliability

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

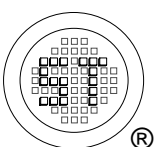
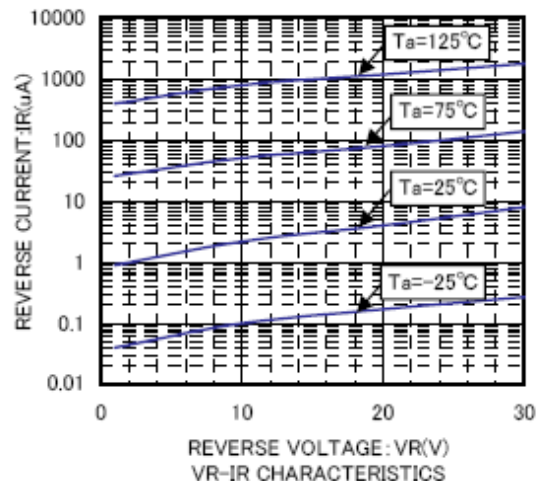
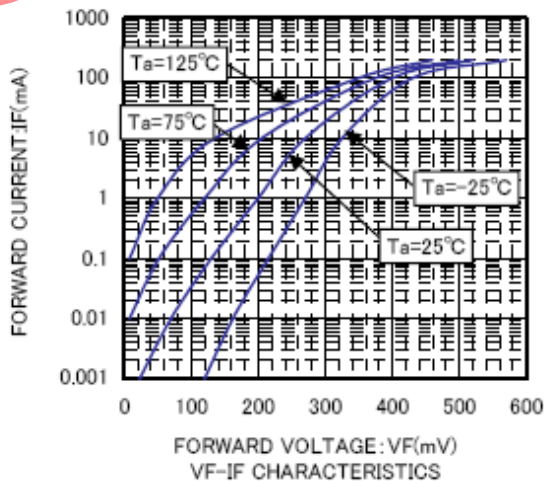


Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	30	V
Average Rectified Forward Current	I_o	100	mA
Peak Forward Surge Current (60 Hz for 1 cyc.)	I_{FSM}	0.5	A
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 40 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 10\text{ mA}$	V_F	0.35	V
Reverse Current at $V_R = 10\text{ V}$	I_R	7	μA



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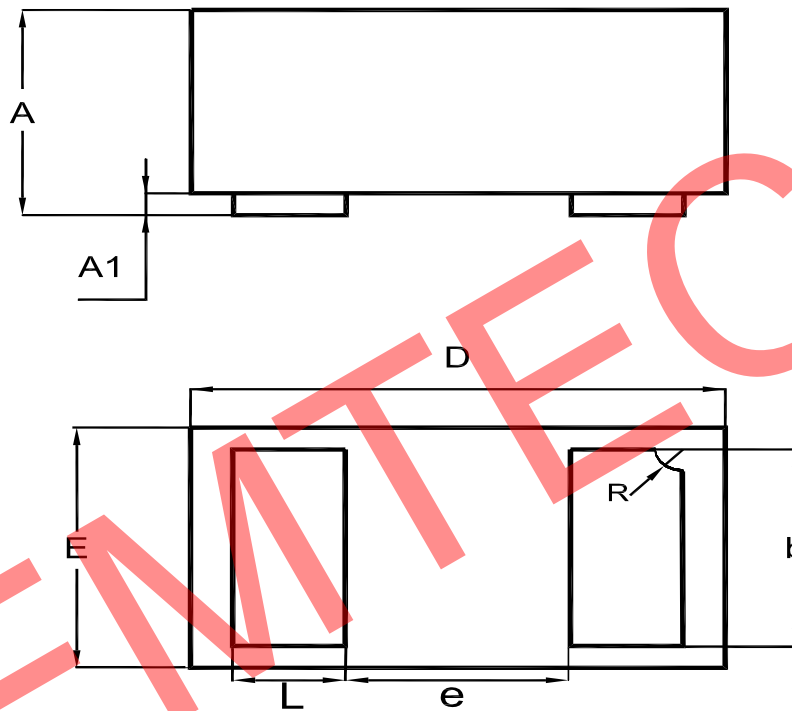


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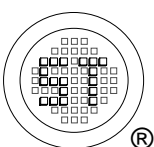
PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

DFN1006-2H



UNIT	A	A1	b	D	E	e	L	R
mm	0.51	0.05	0.55	1.075	0.675	0.4	0.3	0.15
	0.46	0	0.45	0.95	0.55		0.2	0.05



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Dated: 21/05/2013 Rev: 02